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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	144
Number of Logic Elements/Cells	1152
Total RAM Bits	12288
Number of I/O	102
Number of Gates	63000
Voltage - Supply	4.5V ~ 5.5V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k20ti144-4n

The logic array consists of logic array blocks (LABs). Each LAB contains eight LEs and a local interconnect. An LE consists of a 4-input look-up table (LUT), a programmable flipflop, and dedicated signal paths for carry and cascade functions. The eight LEs can be used to create medium-sized blocks of logic—8-bit counters, address decoders, or state machines—or combined across LABs to create larger logic blocks. Each LAB represents about 96 usable gates of logic.

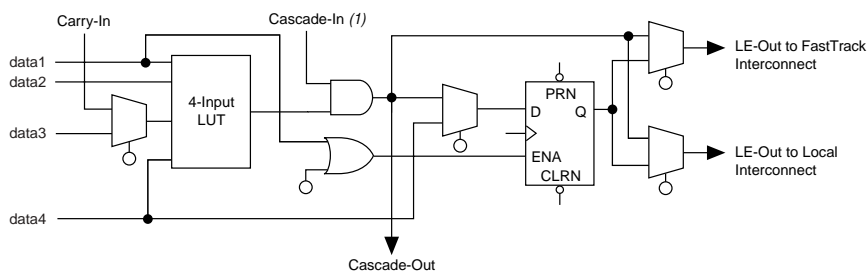
Signal interconnections within FLEX 10K devices and to and from device pins are provided by the FastTrack Interconnect, a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect. Each IOE contains a bidirectional I/O buffer and a flipflop that can be used as either an output or input register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. As inputs, they provide setup times as low as 1.6 ns and hold times of 0 ns; as outputs, these registers provide clock-to-output times as low as 5.3 ns. IOEs provide a variety of features, such as JTAG BST support, slew-rate control, tri-state buffers, and open-drain outputs.

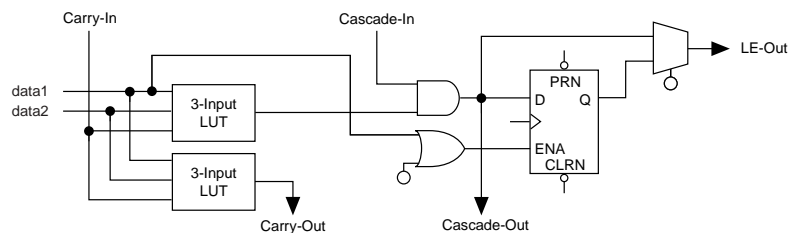
Figure 1 shows a block diagram of the FLEX 10K architecture. Each group of LEs is combined into an LAB; LABs are arranged into rows and columns. Each row also contains a single EAB. The LABs and EABs are interconnected by the FastTrack Interconnect. IOEs are located at the end of each row and column of the FastTrack Interconnect.

Figure 9. FLEX 10K LE Operating Modes

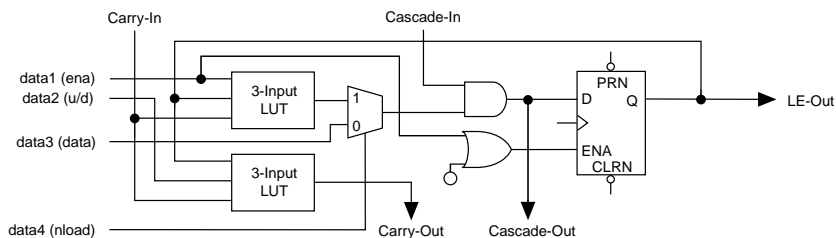
Normal Mode



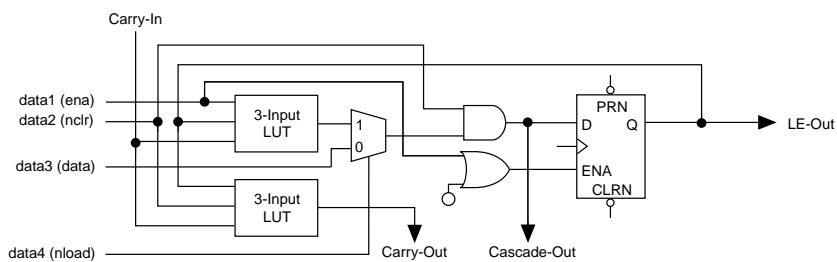
Arithmetic Mode



Up/Down Counter Mode



Clearable Counter Mode



Note:

(1) Packed registers cannot be used with the cascade chain.

During compilation, the Compiler automatically selects the best control signal implementation. Because the clear and preset functions are active-low, the Compiler automatically assigns a logic high to an unused clear or preset.

The clear and preset logic is implemented in one of the following six modes chosen during design entry:

- Asynchronous clear
- Asynchronous preset
- Asynchronous clear and preset
- Asynchronous load with clear
- Asynchronous load with preset
- Asynchronous load without clear or preset

In addition to the six clear and preset modes, FLEX 10K devices provide a chip-wide reset pin that can reset all registers in the device. Use of this feature is set during design entry. In any of the clear and preset modes, the chip-wide reset overrides all other signals. Registers with asynchronous presets may be preset when the chip-wide reset is asserted. Inversion can be used to implement the asynchronous preset. [Figure 10](#) shows examples of how to enter a section of a design for the desired functionality.

Each IOE selects the clock, clear, clock enable, and output enable controls from a network of I/O control signals called the peripheral control bus. The peripheral control bus uses high-speed drivers to minimize signal skew across devices; it provides up to 12 peripheral control signals that can be allocated as follows:

- Up to eight output enable signals
- Up to six clock enable signals
- Up to two clock signals
- Up to two clear signals

If more than six clock enable or eight output enable signals are required, each IOE on the device can be controlled by clock enable and output enable signals driven by specific LEs. In addition to the two clock signals available on the peripheral control bus, each IOE can use one of two dedicated clock pins. Each peripheral control signal can be driven by any of the dedicated input pins or the first LE of each LAB in a particular row. In addition, an LE in a different row can drive a column interconnect, which causes a row interconnect to drive the peripheral control signal. The chip-wide reset signal will reset all IOE registers, overriding any other control signals.

Tables 8 and 9 list the sources for each peripheral control signal, and the rows that can drive global signals. These tables also show how the output enable, clock enable, clock, and clear signals share 12 peripheral control signals.

Table 18. FLEX 10K 5.0-V Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage for internal logic and input buffers	(3), (4)	4.75 (4.50)	5.25 (5.50)	V
V_{CCIO}	Supply voltage for output buffers, 5.0-V operation	(3), (4)	4.75 (4.50)	5.25 (5.50)	V
	Supply voltage for output buffers, 3.3-V operation	(3), (4)	3.00 (3.00)	3.60 (3.60)	V
V_I	Input voltage		−0.5	$V_{CCINT} + 0.5$	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	° C
		For industrial use	−40	85	° C
T_J	Operating temperature	For commercial use	0	85	° C
		For industrial use	−40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 19. FLEX 10K 5.0-V Device DC Operating Conditions *Notes (5), (6)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		2.0		$V_{CCINT} + 0.5$	V
V_{IL}	Low-level input voltage		-0.5		0.8	V
V_{OH}	5.0-V high-level TTL output voltage	$I_{OH} = -4$ mA DC, $V_{CCIO} = 4.75$ V (7)	2.4			V
	3.3-V high-level TTL output voltage	$I_{OH} = -4$ mA DC, $V_{CCIO} = 3.00$ V (7)	2.4			V
	3.3-V high-level CMOS output voltage	$I_{OH} = -0.1$ mA DC, $V_{CCIO} = 3.00$ V (7)	$V_{CCIO} - 0.2$			V
V_{OL}	5.0-V low-level TTL output voltage	$I_{OL} = 12$ mA DC, $V_{CCIO} = 4.75$ V (8)			0.45	V
	3.3-V low-level TTL output voltage	$I_{OL} = 12$ mA DC, $V_{CCIO} = 3.00$ V (8)			0.45	V
	3.3-V low-level CMOS output voltage	$I_{OL} = 0.1$ mA DC, $V_{CCIO} = 3.00$ V (8)			0.2	V
I_I	Input pin leakage current	$V_I = V_{CC}$ or ground (9)	-10		10	μ A
I_{OZ}	Tri-stated I/O pin leakage current	$V_O = V_{CC}$ or ground (9)	-40		40	μ A
I_{CC0}	V_{CC} supply current (standby)	$V_I =$ ground, no load		0.5	10	mA

Table 20. 5.0-V Device Capacitance of EPF10K10, EPF10K20 & EPF10K30 Devices *Note (10)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	$V_{IN} = 0$ V, $f = 1.0$ MHz		8	pF
C_{INCLK}	Input capacitance on dedicated clock pin	$V_{IN} = 0$ V, $f = 1.0$ MHz		12	pF
C_{OUT}	Output capacitance	$V_{OUT} = 0$ V, $f = 1.0$ MHz		8	pF

Table 21. 5.0-V Device Capacitance of EPF10K40, EPF10K50, EPF10K70 & EPF10K100 Devices *Note (10)*

Symbol	Parameter	Conditions	Min	Max	Unit
C_{IN}	Input capacitance	$V_{IN} = 0$ V, $f = 1.0$ MHz		10	pF
C_{INCLK}	Input capacitance on dedicated clock pin	$V_{IN} = 0$ V, $f = 1.0$ MHz		15	pF
C_{OUT}	Output capacitance	$V_{OUT} = 0$ V, $f = 1.0$ MHz		10	pF

Notes to tables:

- (1) See the *Operating Requirements for Altera Devices Data Sheet*.
- (2) Minimum DC input voltage is -0.5 V. During transitions, the inputs may undershoot to -2.0 V for input currents less than 100 mA and periods shorter than 20 ns.
- (3) Numbers in parentheses are for industrial-temperature-range devices.
- (4) Maximum V_{CC} rise time is 100 ms. V_{CC} must rise monotonically.
- (5) Typical values are for $T_A = 25^\circ\text{C}$ and $V_{CC} = 5.0$ V.
- (6) These values are specified under the Recommended Operation Condition shown in Table 18 on page 45.
- (7) The I_{OH} parameter refers to high-level TTL or CMOS output current.
- (8) The I_{OL} parameter refers to low-level TTL or CMOS output current. This parameter applies to open-drain pins as well as output pins.
- (9) This value is specified for normal device operation. The value may vary during power-up.
- (10) Capacitance is sample-tested only.

Figure 20 shows the typical output drive characteristics of FLEX 10K devices with 5.0-V and 3.3-V V_{CCIO} . The output driver is compliant with the 5.0-V *PCI Local Bus Specification, Revision 2.2* (for 5.0-V V_{CCIO}).

Figure 20. Output Drive Characteristics of FLEX 10K Devices

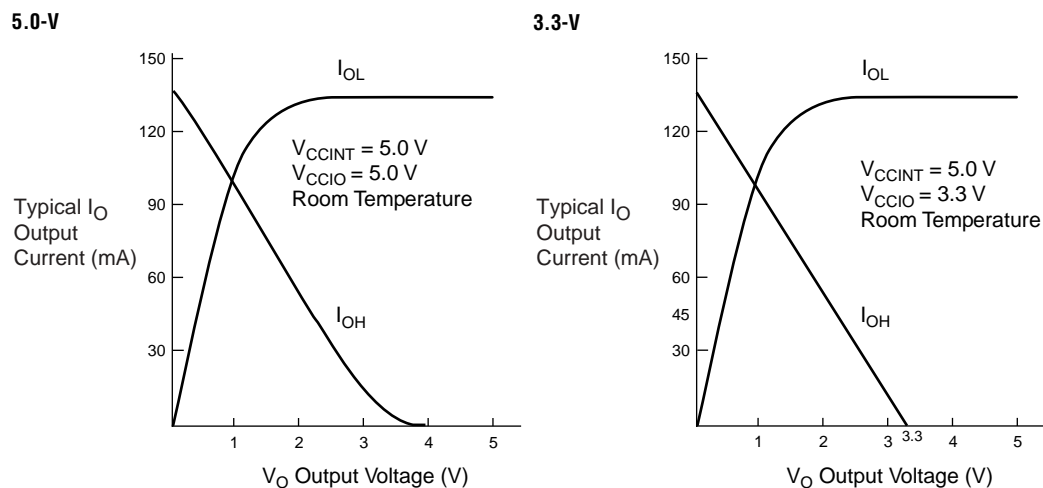
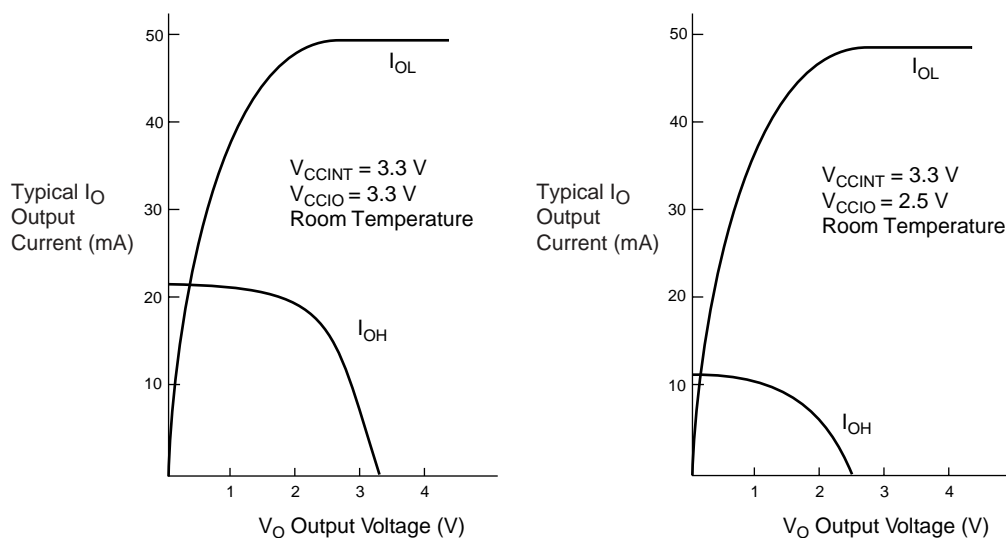


Table 28. FLEX 10KA 3.3-V Device DC Operating Conditions *Notes (6), (7)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level input voltage		1.7 or $0.5 \times V_{CCINT}$, whichever is lower		5.75	V
V_{IL}	Low-level input voltage		-0.5		$0.3 \times V_{CCINT}$	V
V_{OH}	3.3-V high-level TTL output voltage	$I_{OH} = -11$ mA DC, $V_{CCIO} = 3.00$ V (8)	2.4			V
	3.3-V high-level CMOS output voltage	$I_{OH} = -0.1$ mA DC, $V_{CCIO} = 3.00$ V (8)	$V_{CCIO} - 0.2$			V
	3.3-V high-level PCI output voltage	$I_{OH} = -0.5$ mA DC, $V_{CCIO} = 3.00$ to 3.60 V (8)	$0.9 \times V_{CCIO}$			V
	2.5-V high-level output voltage	$I_{OH} = -0.1$ mA DC, $V_{CCIO} = 2.30$ V (8)	2.1			V
		$I_{OH} = -1$ mA DC, $V_{CCIO} = 2.30$ V (8)	2.0			V
		$I_{OH} = -2$ mA DC, $V_{CCIO} = 2.30$ V (8)	1.7			V
V_{OL}	3.3-V low-level TTL output voltage	$I_{OL} = 9$ mA DC, $V_{CCIO} = 3.00$ V (9)			0.45	V
	3.3-V low-level CMOS output voltage	$I_{OL} = 0.1$ mA DC, $V_{CCIO} = 3.00$ V (9)			0.2	V
	3.3-V low-level PCI output voltage	$I_{OL} = 1.5$ mA DC, $V_{CCIO} = 3.00$ to 3.60 V (9)			$0.1 \times V_{CCIO}$	V
	2.5-V low-level output voltage	$I_{OL} = 0.1$ mA DC, $V_{CCIO} = 2.30$ V (9)			0.2	V
		$I_{OL} = 1$ mA DC, $V_{CCIO} = 2.30$ V (9)			0.4	V
		$I_{OL} = 2$ mA DC, $V_{CCIO} = 2.30$ V (9)			0.7	V
I_I	Input pin leakage current	$V_I = 5.3$ V to -0.3 V (10)	-10		10	μ A
I_{OZ}	Tri-stated I/O pin leakage current	$V_O = 5.3$ V to -0.3 V (10)	-10		10	μ A
I_{CC0}	V_{CC} supply current (standby)	$V_I =$ ground, no load		0.3	10	mA
		$V_I =$ ground, no load (11)		10		mA

Figure 23. Output Drive Characteristics for EPF10K250A Device

Timing Model

The continuous, high-performance FastTrack Interconnect routing resources ensure predictable performance and accurate simulation and timing analysis. This predictable performance contrasts with that of FPGAs, which use a segmented connection scheme and therefore have unpredictable performance.

Device performance can be estimated by following the signal path from a source, through the interconnect, to the destination. For example, the registered performance between two LEs on the same row can be calculated by adding the following parameters:

- LE register clock-to-output delay (t_{CO})
- Interconnect delay ($t_{S\text{AMEROW}}$)
- LE look-up table delay (t_{LUT})
- LE register setup time (t_{SU})

The routing delay depends on the placement of the source and destination LEs. A more complex registered path may involve multiple combinatorial LEs between the source and destination LEs.

Table 34. EAB Timing Microparameters *Note (1)*

Symbol	Parameter	Conditions
$t_{EABDATA1}$	Data or address delay to EAB for combinatorial input	
$t_{EABDATA2}$	Data or address delay to EAB for registered input	
t_{EABWE1}	Write enable delay to EAB for combinatorial input	
t_{EABWE2}	Write enable delay to EAB for registered input	
t_{EABCLK}	EAB register clock delay	
t_{EABCO}	EAB register clock-to-output delay	
$t_{EABYPASS}$	Bypass register delay	
t_{EABSU}	EAB register setup time before clock	
t_{EABH}	EAB register hold time after clock	
t_{AA}	Address access delay	
t_{WP}	Write pulse width	
t_{WDSU}	Data setup time before falling edge of write pulse	(5)
t_{WDH}	Data hold time after falling edge of write pulse	(5)
t_{WASU}	Address setup time before rising edge of write pulse	(5)
t_{WAH}	Address hold time after falling edge of write pulse	(5)
t_{WO}	Write enable to data output valid delay	
t_{DD}	Data-in to data-out valid delay	
t_{EABOUT}	Data-out delay	
t_{EABCH}	Clock high time	
t_{EABCL}	Clock low time	

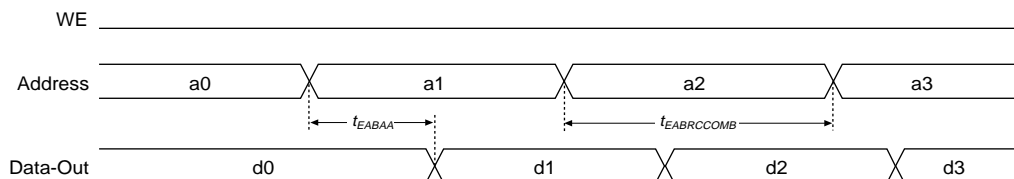
Notes to tables:

- (1) Microparameters are timing delays contributed by individual architectural elements. These parameters cannot be measured explicitly.
- (2) Operating conditions: $V_{CCIO} = 5.0 \text{ V} \pm 5\%$ for commercial use in FLEX 10K devices.
 $V_{CCIO} = 5.0 \text{ V} \pm 10\%$ for industrial use in FLEX 10K devices.
 $V_{CCIO} = 3.3 \text{ V} \pm 10\%$ for commercial or industrial use in FLEX 10KA devices.
- (3) Operating conditions: $V_{CCIO} = 3.3 \text{ V} \pm 10\%$ for commercial or industrial use in FLEX 10K devices.
 $V_{CCIO} = 2.5 \text{ V} \pm 0.2 \text{ V}$ for commercial or industrial use in FLEX 10KA devices.
- (4) Operating conditions: $V_{CCIO} = 2.5 \text{ V}, 3.3 \text{ V}, \text{ or } 5.0 \text{ V}$.
- (5) Because the RAM in the EAB is self-timed, this parameter can be ignored when the \overline{WE} signal is registered.
- (6) EAB macroparameters are internal parameters that can simplify predicting the behavior of an EAB at its boundary; these parameters are calculated by summing selected microparameters.
- (7) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.
- (8) External reference timing parameters are factory-tested, worst-case values specified by Altera. A representative subset of signal paths is tested to approximate typical device applications.
- (9) Contact Altera Applications for test circuit specifications and test conditions.
- (10) These timing parameters are sample-tested only.

Figures 29 and 30 show the asynchronous and synchronous timing waveforms, respectively, for the EAB macroparameters in Table 34.

Figure 29. EAB Asynchronous Timing Waveforms

EAB Asynchronous Read



EAB Asynchronous Write

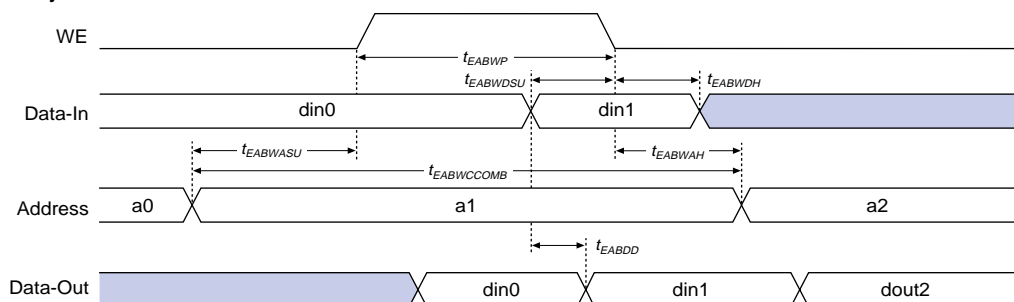


Table 51. EPF10K30, EPF10K40 & EPF10K50 Device EAB Internal Timing Macroparameters*Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{EABAA}		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		17.0		ns
$t_{EABRCREG}$	9.7		11.9		ns
t_{EABWP}	5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		9.0		ns
$t_{EABWCREG}$	13.0		16.0		ns
t_{EABDD}		10.0		12.5	ns
$t_{EABDATACO}$		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		ns
$t_{EABWESU}$	5.5		5.8		ns
t_{EABWEH}	0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.8		ns
t_{EABWDH}	0.0		0.0		ns
$t_{EABWASU}$	2.1		2.7		ns
t_{EABWAH}	0.0		0.0		ns
t_{EABWO}		9.5		11.8	ns

Table 58. EPF10K70 Device IOE Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		0.0		0.0		0.0	ns
t_{IOC}		0.4		0.5		0.7	ns
t_{IOCO}		0.4		0.4		0.9	ns
t_{IOCOMB}		0.0		0.0		0.0	ns
t_{IOSU}	4.5		5.0		6.2		ns
t_{IOH}	0.4		0.5		0.7		ns
t_{IOCLR}		0.6		0.7		1.6	ns
t_{OD1}		3.6		4.0		5.0	ns
t_{OD2}		5.6		6.3		7.3	ns
t_{OD3}		6.9		7.7		8.7	ns
t_{XZ}		5.5		6.2		6.8	ns
t_{ZX1}		5.5		6.2		6.8	ns
t_{ZX2}		7.5		8.5		9.1	ns
t_{ZX3}		8.8		9.9		10.5	ns
t_{INREG}		8.0		9.0		10.2	ns
t_{IOFD}		7.2		8.1		10.3	ns
t_{INCOMB}		7.2		8.1		10.3	ns

Notes to tables:

- (1) All timing parameters are described in Tables 32 through 38 in this data sheet.
- (2) Using an LE to register the signal may provide a lower setup time.
- (3) This parameter is specified by characterization.

Tables 64 through 70 show EPF10K100 device internal and external timing parameters.

Table 64. EPF10K100 Device LE Timing Microparameters <i>Note (1)</i>							
Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.5		1.5		2.0	ns
t_{CLUT}		0.4		0.4		0.5	ns
t_{RLUT}		1.6		1.6		2.0	ns
t_{PACKED}		0.9		0.9		1.3	ns
t_{EN}		0.9		0.9		1.2	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		1.1		1.1		1.4	ns
t_{CGENR}		1.2		1.2		1.5	ns
t_{CASC}		1.1		1.1		1.3	ns
t_C		0.8		0.8		1.0	ns
t_{CO}		1.0		1.0		1.4	ns
t_{COMB}		0.5		0.5		0.7	ns
t_{SU}	2.1		2.1		2.6		ns
t_H	2.3		2.3		3.1		ns
t_{PRE}		1.0		1.0		1.4	ns
t_{CLR}		1.0		1.0		1.4	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 66. EPF10K100 Device EAB Internal Microparameters *Note (1)*

Symbol	-3DX Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.5		1.5		1.9	ns
$t_{EABDATA2}$		4.8		4.8		6.0	ns
t_{EABWE1}		1.0		1.0		1.2	ns
t_{EABWE2}		5.0		5.0		6.2	ns
t_{EABCLK}		1.0		1.0		2.2	ns
t_{EABCO}		0.5		0.5		0.6	ns
$t_{EABYPASS}$		1.5		1.5		1.9	ns
t_{EABSU}	1.5		1.5		1.8		ns
t_{EABH}	2.0		2.0		2.5		ns
t_{AA}		8.7		8.7		10.7	ns
t_{WP}	5.8		5.8		7.2		ns
t_{WDSU}	1.6		1.6		2.0		ns
t_{WDH}	0.3		0.3		0.4		ns
t_{WASU}	0.5		0.5		0.6		ns
t_{WAH}	1.0		1.0		1.2		ns
t_{WO}		5.0		5.0		6.2	ns
t_{DD}		5.0		5.0		6.2	ns
t_{EABOUT}		0.5		0.5		0.6	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	5.8		5.8		7.2		ns

Table 74. EPF10K50V Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{EABAA}		9.5		13.6		16.5		20.8	ns
$t_{EABRCCOMB}$	9.5		13.6		16.5		20.8		ns
$t_{EABRCREG}$	6.1		8.8		10.8		13.4		ns
t_{EABWP}	6.0		4.9		6.0		7.4		ns
$t_{EABWCCOMB}$	6.2		6.1		7.5		9.2		ns
$t_{EABWCREG}$	12.0		11.6		14.2		17.4		ns
t_{EABDD}		6.8		9.7		11.8		14.9	ns
$t_{EABDATACO}$		1.0		1.4		1.8		2.2	ns
$t_{EABDATASU}$	5.3		4.6		5.6		6.9		ns
$t_{EABDATAH}$	0.0		0.0		0.0		0.0		ns
$t_{EABWESU}$	4.4		4.8		5.8		7.2		ns
t_{EABWEH}	0.0		0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.8		1.1		1.4		2.1		ns
t_{EABWDH}	0.0		0.0		0.0		0.0		ns
$t_{EABWASU}$	4.5		4.6		5.6		7.4		ns
t_{EABWAH}	0.0		0.0		0.0		0.0		ns
t_{EABWO}		5.1		9.4		11.4		14.0	ns

Table 89. EPF10K10A Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		4.2		5.0		6.5	ns
t_{DIN2LE}		2.2		2.6		3.4	ns
$t_{DIN2DATA}$		4.3		5.2		7.1	ns
$t_{DCLK2IOE}$		4.2		4.9		6.6	ns
$t_{DCLK2LE}$		2.2		2.6		3.4	ns
$t_{SAMELAB}$		0.1		0.1		0.2	ns
$t_{SAMEROW}$		2.2		2.4		2.9	ns
$t_{SAMECOLUMN}$		0.8		1.0		1.4	ns
$t_{DIFFROW}$		3.0		3.4		4.3	ns
$t_{TWOROWS}$		5.2		5.8		7.2	ns
$t_{LEPERIPH}$		1.8		2.2		2.8	ns
$t_{LABCARRY}$		0.5		0.5		0.7	ns
$t_{LABCASC}$		0.9		1.0		1.5	ns

Table 90. EPF10K10A External Reference Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		10.0		12.0		16.0	ns
t_{INSU} (2), (3)	1.6		2.1		2.8		ns
t_{INH} (3)	0.0		0.0		0.0		ns
t_{OUTCO} (3)	2.0	5.8	2.0	6.9	2.0	9.2	ns

Table 91. EPF10K10A Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.4		3.3		4.5		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	5.8	2.0	6.9	2.0	9.2	ns
$t_{XZBIDIR}$		6.3		7.5		9.9	ns
$t_{ZXBIDIR}$		6.3		7.5		9.9	ns

Table 110. EPF10K250A Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		7.8		8.5		9.4	ns
t_{DIN2LE}		2.7		3.1		3.5	ns
$t_{DIN2DATA}$		1.6		1.6		1.7	ns
$t_{DCLK2IOE}$		3.6		4.0		4.6	ns
$t_{DCLK2LE}$		2.7		3.1		3.5	ns
$t_{SAMELAB}$		0.2		0.3		0.3	ns
$t_{SAMEROW}$		6.7		7.3		8.2	ns
$t_{SAMECOLUMN}$		2.5		2.7		3.0	ns
$t_{DIFFROW}$		9.2		10.0		11.2	ns
$t_{TWOROWS}$		15.9		17.3		19.4	ns
$t_{LEPERIPH}$		7.5		8.1		8.9	ns
$t_{LABCARRY}$		0.3		0.4		0.5	ns
$t_{LABCASC}$		0.4		0.4		0.5	ns

Table 111. EPF10K250A Device External Reference Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		15.0		17.0		20.0	ns
t_{INSU} (2), (3)	6.9		8.0		9.4		ns
t_{INH} (3)	0.0		0.0		0.0		ns
t_{OUTCO} (3)	2.0	8.0	2.0	8.9	2.0	10.4	ns

Table 112. EPF10K250A Device External Bidirectional Timing Parameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	9.3		10.6		12.7		ns
$t_{INHBIDIR}$	0.0		0.0		0.0		ns
$t_{OUTCOBIDIR}$	2.0	8.0	2.0	8.9	2.0	10.4	ns
$t_{XZBIDIR}$		10.8		12.2		14.2	ns
$t_{ZXBIDIR}$		10.8		12.2		14.2	ns

Multiple FLEX 10K devices can be configured in any of the five configuration schemes by connecting the configuration enable (nCE) and configuration enable output (nCEO) pins on each device.

Table 116. Data Sources for Configuration

Configuration Scheme	Data Source
Configuration device	EPC1, EPC2, EPC16, or EPC1441 configuration device
Passive serial (PS)	BitBlaster, MasterBlaster, or ByteBlasterMV download cable, or serial data source
Passive parallel asynchronous (PPA)	Parallel data source
Passive parallel synchronous (PPS)	Parallel data source
JTAG	BitBlaster, MasterBlaster, or ByteBlasterMV download cable, or microprocessor with Jam STAPL file or Jam Byte-Code file

Device Pin-Outs

See the Altera web site (<http://www.altera.com>) or the Altera Digital Library for pin-out information.

Revision History

The information contained in the *FLEX 10K Embedded Programmable Logic Device Family Data Sheet* version 4.2 supersedes information published in previous versions.

Version 4.2 Changes

The following change was made to version 4.2 of the *FLEX 10K Embedded Programmable Logic Device Family Data Sheet*: updated [Figure 13](#).

Version 4.1 Changes

The following changes were made to version 4.1 of the *FLEX 10K Embedded Programmable Logic Device Family Data Sheet*.

- Updated General Description section
- Updated I/O Element section
- Updated SameFrame Pin-Outs section
- Updated Figure 16
- Updated Tables 13 and 116
- Added Note 9 to Table 19
- Added Note 10 to Table 24
- Added Note 10 to Table 28



101 Innovation Drive
San Jose, CA 95134
(408) 544-7000
<http://www.altera.com>
Applications Hotline:
(800) 800-EPLD
Customer Marketing:
(408) 544-7104
Literature Services:
lit_req@altera.com

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